

Claims

- [c1] 1. A photoelectric device grinding process, comprising the steps of:
providing a wafer having a plurality of chip units thereon, wherein the surface of each chip unit has at least a photoelectric device;
providing some glue having a plurality of spacers embedded therein;
attaching a dielectric substrate over the photoelectric device on the surface of the wafer through the glue, wherein the glue and the spacers are disposed between the dielectric substrate and the wafer such that the spacers maintain a constant gap between the dielectric substrate and the wafer; and
grinding the surface of the dielectric substrate away from the wafer or the surface of the wafer away from the dielectric substrate.
- [c2] 2. The photoelectric device grinding process of claim 1, wherein the photoelectric device comprises an image sensor.
- [c3] 3. The photoelectric device grinding process of claim 1, wherein the photoelectric device comprises a micro-

mechanical structure.

- [c4] 4. The photoelectric device grinding process of claim 3, wherein the micro-mechanical structure protrudes from the surface of the wafer by a height smaller than the gap between the dielectric substrate and the wafer.
- [c5] 5. The photoelectric device grinding process of claim 1, wherein the glue comprises ultraviolet cured plastic.
- [c6] 6. The photoelectric device grinding process of claim 1, wherein the material constituting the spacers comprises silicon oxide.
- [c7] 7. The photoelectric device grinding process of claim 1, wherein the step of grinding the dielectric substrate or the wafer comprises mechanical grinding.
- [c8] 8. The photoelectric device grinding process of claim 1, wherein the dielectric substrate comprises a glass substrate or a silicon substrate.
- [c9] 9. The photoelectric device grinding process of claim 1, wherein the glue, each chip unit and the dielectric substrate together form at least a sealed chamber such that the photoelectric device is enclosed within the sealed chamber.
- [c10] 10. A device grinding process, comprising the steps of:

providing a wafer having a plurality of chip units thereon, wherein the surface of each chip unit has at least a device;
attaching a dielectric substrate over the device on the surface of the wafer such that a constant gap is maintained between the dielectric substrate and the wafer;
and
grinding the surface of the dielectric substrate away from the wafer or the surface of the wafer away from the dielectric substrate.

[c11] 11. The device grinding process of claim 10, wherein the device comprises a photoelectric device.

[c12] 12. The device grinding process of claim 11, wherein the photoelectric device comprises an image sensor.

[c13] 13. The device grinding process of claim 11, wherein each photoelectric device has a micro-mechanical structure.

[c14] 14. The device grinding process of claim 13, wherein the micro-mechanical structure protrudes from the surface of the wafer by a height smaller than the gap between the dielectric substrate and the wafer.

[c15] 15. The device grinding process of claim 10, wherein the step attaching the dielectric substrate to the wafer com-

prises applying some glue.

- [c16] 16. The device grinding process of claim 15, wherein the glue further comprises a plurality of spacers embedded therein.
- [c17] 17. The device grinding process of claim 16, wherein the material constituting the spacers comprises silicon oxide.
- [c18] 18. The device grinding process of claim 15, wherein the material constituting the glue is selected from a group consisting of ultraviolet cured plastic and epoxy resin.
- [c19] 19. The device grinding process of claim 10, wherein the step of grinding the dielectric substrate or the wafer comprises mechanical grinding.
- [c20] 20. The device grinding process of claim 10, wherein the dielectric substrate comprises a glass substrate or a silicon substrate.
- [c21] 21. The device grinding process of claim 10, wherein the chip unit and the dielectric substrate together form at least a sealed chamber such that the device is enclosed within the sealed chamber.